# NL17SHT08

# 2-Input AND Gate / CMOS Logic Level Shifter

The NL17SHT08 is an advanced high speed CMOS 2-input AND gate fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output.

The device input is compatible with TTL-type input thresholds and the output has a full 5 V CMOS level output swing. The input protection circuitry on this device allows overvoltage tolerance on the input, allowing the device to be used as a logic-level translator from 3 V CMOS logic to 5 V CMOS Logic or from 1.8 V CMOS logic to 3 V CMOS Logic while operating at the high-voltage power supply.

The NL17SHT08 input structure provides protection when voltages up to 7 V are applied, regardless of the supply voltage. This allows the NL17SHT08 to be used to interface 5 V circuits to 3 V circuits. The output structures also provide protection when  $V_{CC} = 0$  V. These input and output structures help prevent device destruction caused by supply voltage – input/output voltage mismatch, battery backup, hot insertion, etc.

#### Features

- High Speed:  $t_{PD} = 3.5$  ns (Typ) at  $V_{CC} = 5$  V
- Low Power Dissipation:  $I_{CC} = 1 \ \mu A$  (Max) at  $T_A = 25^{\circ}C$
- TTL-Compatible Inputs:  $V_{IL} = 0.8 V$ ;  $V_{IH} = 2 V$
- CMOS–Compatible Outputs:  $V_{OH} > 0.8 V_{CC}$ ;  $V_{OL} < 0.1 V_{CC}$  @Load
- Power Down Protection Provided on Inputs and Outputs
- Balanced Propagation Delays
- Pin and Function Compatible with Other Standard Logic Families
- These are Pb-Free Devices

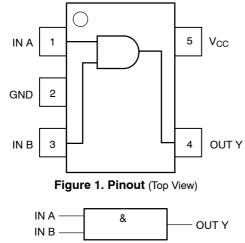
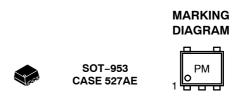


Figure 2. Logic Symbol



## **ON Semiconductor**<sup>®</sup>

http://onsemi.com



P = Specific Device Code M = Month Code

PIN ASSIGNMENT							
1 IN A							
2 GND							
3 IN B							
4	OUT Y						
5 V <sub>CC</sub>							

#### **FUNCTION TABLE**

Inp	uts	Output
Α	В	Y
L	L	L
L	н	L
н	L	L
Н	Н	н

#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

## MAXIMUM RATINGS

Symbol	Characteristics	Value	Unit
V <sub>CC</sub>	DC Supply Voltage	-0.5 to +7.0	V
V <sub>IN</sub>	DC Input Voltage	-0.5 to +7.0	V
V <sub>OUT</sub>	DC Output Voltage V <sub>CC</sub> = 0 High or Low State	-0.5 to 7.0 -0.5 to V <sub>CC</sub> + 0.5	V
Ι <sub>ΙΚ</sub>	Input Diode Current	-20	mA
I <sub>OK</sub>	$\label{eq:output} Output \ Diode \ Current \qquad \qquad V_{OUT} < GND; \ V_{OUT} > V_{CC}$	±20	mA
I <sub>OUT</sub>	DC Output Current	±25	mA
I <sub>CC</sub>	DC Supply Current, V <sub>CC</sub> and GND	50	mA
PD	Power dissipation in still air	50	mW
ΤL	Lead temperature, 1 mm from case for 10 s	260	°C
TJ	Junction temperature under bias	+150	°C
T <sub>stg</sub>	Storage temperature	-65 to +150	°C
I <sub>Latchup</sub>	Latchup Performance Above V <sub>CC</sub> and Below GND at 125°C (Note 1)	±100	mA

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Tested to EIA/JESD78

### **RECOMMENDED OPERATING CONDITIONS**

Symbol	Characteristics	Min	Max	Unit	
V <sub>CC</sub>	DC Supply Voltage	3.0	5.5	V	
V <sub>IN</sub>	DC Input Voltage	0.0	5.5	V	
V <sub>OUT</sub>	DC Output Voltage High or	V <sub>CC</sub> = 0 _ow State	0.0 0.0	5.5 V <sub>CC</sub>	V
T <sub>A</sub>	Operating Temperature Range		-55	+125	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise and Fall Time $V_{CC} = 3.3$ $V_{CC} = 5.0$	$\begin{array}{c} V\pm0.3~V\\ V\pm0.5~V \end{array}$	0 0	100 20	ns/V

#### Device Junction Temperature versus Time to 0.1% Bond Failures

Junction Temperature °C	Time, Hours	Time, Years
80	1,032,200	117.8
90	419,300	47.9
100	178,700	20.4
110	79,600	9.4
120	37,000	4.2
130	17,800	2.0
140	8,900	1.0

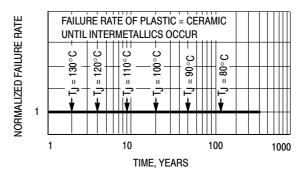


Figure 3. Failure Rate vs. Time Junction Temperature

			v <sub>cc</sub>	T <sub>A</sub> = 25°C		<b>TA</b> ≤	85°C	$-55 \leq T_{A} \leq 125^{\circ}C$			
Symbol	Parameter	Test Conditions	•cc (V)	Min	Тур	Max	Min	Max	Min	Max	Unit
V <sub>IH</sub>	Minimum High–Level Input Voltage		3.0 4.5 5.5	1.4 2.0 2.0			1.4 2.0 2.0		1.4 2.0 2.0		V
V <sub>IL</sub>	Maximum Low-Level Input Voltage		3.0 4.5 5.5			0.53 0.8 0.8		0.53 0.8 0.8		0.53 0.8 0.8	V
$V_{OH}$ Minimum High-Level Output Voltage $V_{IN} = V_{IH}$ or $V_{IL}$	Output Voltage	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -50 \ \mu\text{A}$	3.0 4.5	2.9 4.4	3.0 4.5		2.9 4.4		2.9 4.4		V
	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	$\label{eq:VIN} \begin{array}{l} V_{IN} = V_{IH} \text{ or } V_{IL} \\ I_{OH} = -4 \text{ mA} \\ I_{OH} = -8 \text{ mA} \end{array}$	3.0 4.5	2.58 3.94			2.48 3.80		2.34 3.66		V
OL	Maximum Low-Level Output Voltage	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 50 \ \mu A$	3.0 4.5		0.0 0.0	0.1 0.1		0.1 0.1		0.1 0.1	V
	$V_{IN} = V_{IH}$ or $V_{IL}$	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 4 \text{ mA}$ $I_{OL} = 8 \text{ mA}$	3.0 4.5			0.36 0.36		0.44 0.44		0.52 0.52	V
I <sub>IN</sub>	Maximum Input Leakage Current	V <sub>IN</sub> = 5.5 V or GND	0 to 5.5			±0.1		±1.0		±1.0	μΑ
I <sub>CC</sub>	Maximum Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND	5.5			1.0		20		40	μA
I <sub>CCT</sub>	Quiescent Supply Current	Input: V <sub>IN</sub> = 3.4 V	5.5			1.35		1.50		1.65	mA
I <sub>OPD</sub>	Output Leakage Current	V <sub>OUT</sub> = 5.5 V	0.0			0.5		5.0		10	μΑ

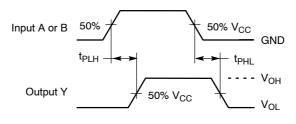
## DC ELECTRICAL CHARACTERISTICS

# AC ELECTRICAL CHARACTERISTICS $\mathrm{C}_{load}$ = 50 pF, Input $t_{r}$ = $t_{f}$ = 3.0 ns

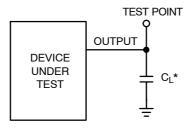
				Т	A = 25°	С	<b>T</b> <sub>A</sub> ≤	85°C	-55 ≤ T <sub>A</sub>	≤ 125°C	
Symbol	Parameter	Test Condi	tions	Min	Тур	Max	Min	Max	Min	Max	Unit
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, Input A or B to Y	$V_{CC}=3.3\pm0.3~V$	C <sub>L</sub> = 15 pF C <sub>L</sub> = 50 pF		4.1 5.9	8.8 12.3		10.5 14.0		12.5 16.5	ns
		$V_{CC} = 5.0 \pm 0.5 \text{ V}$	C <sub>L</sub> = 15 pF C <sub>L</sub> = 50 pF		3.5 4.2	5.9 7.9		7.0 9.0		9.0 11.0	
C <sub>IN</sub>	Maximum Input Capacit- ance				5.5	10		10		10	pF
	Typical @ 25°C, V <sub>CC</sub> = 5.0 V										
CPD	Power Dissipation Capacit	ance (Note 2)					11				pF

2.  $C_{PD}$  is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation:  $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC}$ .  $C_{PD}$  is used to determine the no-load dynamic power consumption;  $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$ .

# NL17SHT08







\*Includes all probe and jig capacitance

Figure 5. Test Circuit

### **ORDERING INFORMATION**

Device	Device Package	
NL17SHT08P5T5G	SOT-953 (Pb-Free)	8000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

SCALE 4:1

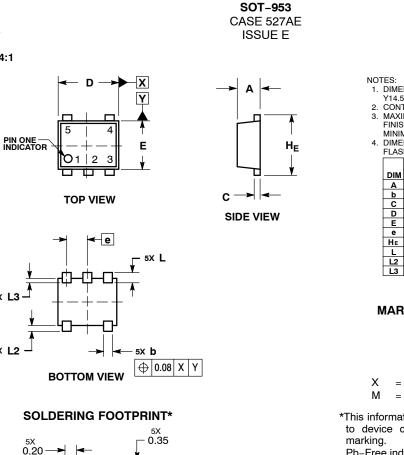
5X L3

5X L2

PACKAGE OUTLINE

0.35 PITCH





#### DATE 02 AUG 2011

- NOTES: 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. 2. CONTROLLING DIMENSION: MILLIMETERS 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL. 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS							
DIM	MIN NOM MAX							
Α	0.34	0.37	0.40					
b	0.10	0.15	0.20					
С	0.07	0.12	0.17					
D	0.95	1.00	1.05					
E	0.75	0.85						
е		0.35 BS	С					
ΗE	0.95	1.00	1.05					
L	(	0.175 RE	F					
L2	0.05	0.10	0.15					
L3			0.15					

# GENERIC **MARKING DIAGRAM\***

= Specific Device Code

= Month Code

\*This information is generic. Please refer to device data sheet for actual part

Pb-Free indicator, "G" or microdot " .", may or may not be present.

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

L

DIMENSIONS: MILLIMETERS

1.20

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